Timo Sajavaara

List of Publications by Year
in descending order

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232 papers	7,707 citations	38742 50 h-index	66911 78 g-index
241 all docs	241 docs citations	241 times ranked	7129 citing authors

#	Article	IF	Citations
1	Atomic Layer Deposition of Oxide Thin Films with Metal Alkoxides as Oxygen Sources. Science, 2000, 288, 319-321.	12.6	452
2	Atomic Layer Deposition of Platinum Thin Films. Chemistry of Materials, 2003, 15, 1924-1928.	6.7	360
3	Effect of water dose on the atomic layer deposition rate of oxide thin films. Thin Solid Films, 2000, 368, 1-7.	1.8	239
4	Atomic Layer Deposition of Photocatalytic TiO2 Thin Films from Titanium Tetramethoxide and Water. Chemical Vapor Deposition, 2004, 10, 143-148.	1.3	204
5	Atomic Layer Deposition of Hafnium Dioxide Films from Hafnium Tetrakis(ethylmethylamide) and Water. Chemical Vapor Deposition, 2002, 8, 199-204.	1.3	192
6	Aluminum oxide from trimethylaluminum and water by atomic layer deposition: The temperature dependence of residual stress, elastic modulus, hardness and adhesion. Thin Solid Films, 2014, 552, 124-135.	1.8	155
7	Detection efficiency of time-of-flight energy elastic recoil detection analysis systems. Nuclear Instruments & Methods in Physics Research B, 1999, 149, 477-489.	1.4	148
8	Potku â€" New analysis software for heavy ion elastic recoil detection analysis. Nuclear Instruments & Methods in Physics Research B, 2014, 331, 34-41.	1.4	141
9	Comparison of hafnium oxide films grown by atomic layer deposition from iodide and chloride precursors. Thin Solid Films, 2002, 416, 72-79.	1.8	128
10	Short-ranged structural rearrangement and enhancement of mechanical properties of organosilicate glasses induced by ultraviolet radiation. Journal of Applied Physics, 2006, 99, 053511.	2.5	119
11	Atomic layer deposition of polyimide thin films. Journal of Materials Chemistry, 2007, 17, 664-669.	6.7	118
12	Properties of AlN grown by plasma enhanced atomic layer deposition. Applied Surface Science, 2011, 257, 7827-7830.	6.1	112
13	Plasma-Enhanced Atomic Layer Deposition of Silver Thin Films. Chemistry of Materials, 2011, 23, 2901-2907.	6.7	106
14	Atomic Layer Deposition of SrTiO3 Thin Films from a Novel Strontium Precursor-Strontium-bis(tri-isopropyl cyclopentadienyl). Chemical Vapor Deposition, 2001, 7, 75-80.	1.3	105
15	Low-Temperature ALE Deposition of Y2O3 Thin Films from Î²-Diketonate Precursors. Chemical Vapor Deposition, 2001, 7, 44-50.	1.3	97
16	Low-temperature atomic layer deposition of ZnO thin films: Control of crystallinity and orientation. Thin Solid Films, 2011, 519, 5319-5322.	1.8	90
17	Overview of material re-deposition and fuel retention studies at JET with the Gas Box divertor. Nuclear Fusion, 2006, 46, 350-366.	3.5	89
18	Surface-controlled growth of LaAlO3 thin films by atomic layer epitaxy. Journal of Materials Chemistry, 2001, 11, 2340-2345.	6.7	87

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19	Atomic layer deposition of lithium containing thin films. Journal of Materials Chemistry, 2009, 19, 8767.	6.7	81
20	Gadolinium oxide thin films by atomic layer deposition. Journal of Crystal Growth, 2005, 285, 191-200.	1.5	76
21	Atomic layer deposition of hafnium dioxide thin films from hafnium tetrakis(dimethylamide) and water. Thin Solid Films, 2005, 491, 328-338.	1.8	76
22	Studies on atomic layer deposition of MOF-5 thin films. Microporous and Mesoporous Materials, 2013, 182, 147-154.	4.4	76
23	ZrO2 Thin Films Grown on Silicon Substrates by Atomic Layer Deposition with Cp2Zr(CH3)2 and Water as Precursors. Chemical Vapor Deposition, 2003, 9, 207-212.	1.3	71
24	Low-Temperature Atomic Layer Deposition of Crystalline and Photoactive Ultrathin Hematite Films for Solar Water Splitting. ACS Nano, 2015, 9, 11775-11783.	14.6	70
25	Enhanced growth rate in atomic layer epitaxy deposition of magnesium oxide thin films. Journal of Materials Chemistry, 2000, 10, 1857-1861.	6.7	69
26	Atomic layer deposition of rare earth oxides: erbium oxide thin films from Î²-diketonate and ozone precursors. Journal of Alloys and Compounds, 2004, 374, 124-128.	5.5	69
27	Low Temperature Growth of High Purity, Low Resistivity Copper Films by Atomic Layer Deposition. Chemistry of Materials, 2011, 23, 4417-4419.	6.7	69
28	Time-of-flight â€" Energy spectrometer for elemental depth profiling â€" JyvÃskylÃ design. Nuclear Instruments & Methods in Physics Research B, 2014, 337, 55-61.	1.4	68
29	Atomic layer deposition and characterization of biocompatible hydroxyapatite thin films. Thin Solid Films, 2009, 517, 5819-5824.	1.8	67
30	Surface-Controlled Deposition of Sc2O3Thin Films by Atomic Layer Epitaxy Using Î²-Diketonate and Organometallic Precursors. Chemistry of Materials, 2001, 13, 4701-4707.	6.7	66
31	Analysis of ALD-processed thin films by ion-beam techniques. Analytical and Bioanalytical Chemistry, 2005, 382, 1791-1799.	3.7	66
32	Thermal and plasma enhanced atomic layer deposition of SiO2 using commercial silicon precursors. Thin Solid Films, 2014, 558, 93-98.	1.8	66
33	Atomic Layer Deposition of Spinel Lithium Manganese Oxide by Film-Body-Controlled Lithium Incorporation for Thin-Film Lithium-Ion Batteries. Journal of Physical Chemistry C, 2014, 118, 1258-1268.	3.1	66
34	Review Article: Recommended reading list of early publications on atomic layer depositionâ€"Outcome of the â€œVirtual Project on the History of ALDâ€. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	65
35	Effect of selected atomic layer deposition parameters on the structure and dielectric properties of hafnium oxide films. Journal of Applied Physics, 2004, 96, 5298-5307.	2.5	64
36	Controlled growth of HfO2 thin films by atomic layer deposition from cyclopentadienyl-type precursor and water. Journal of Materials Chemistry, 2005, 15, 2271.	6.7	64

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37	Monte Carlo simulation of multiple and plural scattering in elastic recoil detection. Nuclear Instruments & Methods in Physics Research B, 2001, 174, 163-172.	1.4	63
38	Properties of hafnium oxide films grown by atomic layer deposition from hafnium tetraiodide and oxygen. Journal of Applied Physics, 2002, 92, 5698-5703.	2.5	63
39	Evidence of quantum phase slip effect in titanium nanowires. Physical Review B, 2012, 85, .	3.2	62
40	Reduction of Copper Oxide Film to Elemental Copper. Journal of the Electrochemical Society, 2005, 152, G122.	2.9	61
41	Radical-Enhanced Atomic Layer Deposition of Metallic Copper Thin Films. Journal of the Electrochemical Society, 2005, 152, G25.	2.9	59
42	One-Step Electrodeposition of Cu[sub 2âˆ’x]Se and CuInSe[sub 2] Thin Films by the Induced Co-deposition Mechanism. Journal of the Electrochemical Society, 2000, 147, 1080.	2.9	58
43	Corrosion Protection of Steel with Oxide Nanolaminates Grown by Atomic Layer Deposition. Journal of the Electrochemical Society, 2011, 158, C369.	2.9	58
44	Atomic Layer Deposition of Hafnium Dioxide Films from 1-Methoxy-2-methyl-2-propanolate Complex of Hafnium. Chemistry of Materials, 2003, 15, 1722-1727.	6.7	57
45	Generalized Noise Study of Solid-State Nanopores at Low Frequencies. ACS Sensors, 2017, 2, 300-307.	7.8	57
46	Deposition of yttria-stabilized zirconia thin films by atomic layer epitaxy from Î²-diketonate and organometallic precursors. Journal of Materials Chemistry, 2002, 12, 442-448.	6.7	55
47	Atomic Layer Deposition and Properties of Lanthanum Oxide and Lanthanum-AluminumÂOxide Films. Chemical Vapor Deposition, 2006, 12, 158-164.	1.3	55
48	Atomic layer deposition of ferroelectric LiNbO₃. Journal of Materials Chemistry C, 2013, 1, 4283-4290.	5.5	54
49	Atomic Layer Deposition of Ta(Al)N(C) Thin Films Using Trimethylaluminum as a Reducing Agent. Journal of the Electrochemical Society, 2001, 148, G566.	2.9	52
50	Studies of impurity deposition/implantation in JET divertor tiles using SIMS and ion beam techniques. Fusion Engineering and Design, 2003, 66-68, 219-224.	1.9	52
51	Evaluation of a Praseodymium Precursor for Atomic Layer Deposition of Oxide Dielectric Films. Chemistry of Materials, 2004, 16, 5162-5168.	6.7	52
52	Atomic Layer Deposition of Ruthenium Films from (Ethylcyclopentadienyl)(pyrrolyl)ruthenium and Oxygen. Journal of the Electrochemical Society, 2011, 158, D158.	2.9	52
53	Variation of lattice constant and cluster formation in GaAsBi. Journal of Applied Physics, 2013, 114, 243504.	2.5	52
54	Atomic Layer Deposition of Titanium Oxide from TiI4 and H2O2. Chemical Vapor Deposition, 2000, 6, 303-310.	1.3	51

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55	Controlling the Crystallinity and Roughness of Atomic Layer Deposited Titanium Dioxide Films. Journal of Nanoscience and Nanotechnology, 2011, 11, 8101-8107.	0.9	51
56	Atomic Layer Deposition of Hafnium Dioxide Films Using Hafnium Bis(2-butanolate)bis(1-methoxy-2-methyl-2-propanolate) and Water. Chemical Vapor Deposition, 2003, 9, 315-320.	1.3	49
57	Atomic layer deposition of LixTiyOz thin films. RSC Advances, 2013, 3, 7537-7542.	3.6	49
58	Evaluation and Comparison of Novel Precursors for Atomic Layer Deposition of Nb2O5Thin Films. Chemistry of Materials, 2012, 24, 975-980.	6.7	47
59	Antibacterial and barrier properties of oriented polymer films with ZnO thin films applied with atomic layer deposition at low temperatures. Thin Solid Films, 2014, 562, 331-337.	1.8	47
60	Iridium metal and iridium oxide thin films grown by atomic layer deposition at low temperatures. Journal of Materials Chemistry, 2011, 21, 16488.	6.7	46
61	Atomic Layer Deposition of WO₃ Thin Films using W(CO)₆ and O₃ Precursors. Chemical Vapor Deposition, 2012, 18, 245-248.	1.3	45
62	Self-starting stretched-pulse fiber laser mode locked and stabilized with slow and fast semiconductor saturable absorbers. Optics Letters, 2001, 26, 1809.	3.3	43
63	Stabilizing organic photocathodes by low-temperature atomic layer deposition of TiO₂. Sustainable Energy and Fuels, 2017, 1, 1915-1920.	4.9	43
64	Low temperature atomic layer deposition of noble metals using ozone and molecular hydrogen as reactants. Thin Solid Films, 2013, 531, 243-250.	1.8	42
65	Atomic Layer Deposition of Osmium. Chemistry of Materials, 2012, 24, 55-60.	6.7	41
66	X-Ray absorption studies of cubic boronâ€“carbonâ€“nitrogen films grown by ion beam assisted evaporation. Diamond and Related Materials, 2001, 10, 1165-1169.	3.9	40
67	Atomic layer deposition of Al2O3, ZrO2, Ta2O5, and Nb2O5 based nanolayered dielectrics. Journal of Non-Crystalline Solids, 2002, 303, 35-39.	3.1	40
68	Linear Energy Transfer of Heavy Ions in Silicon. IEEE Transactions on Nuclear Science, 2007, 54, 1158-1162.	2.0	40
69	Control of Oxygen Nonstoichiometry and Magnetic Property of MnCo₂O₄ Thin Films Grown by Atomic Layer Deposition. Chemistry of Materials, 2010, 22, 6297-6300.	6.7	39
70	<i>Tert</i>-butylamine and Allylamine as Reductive Nitrogen Sources in Atomic Layer Deposition of TaN Thin Films. Journal of Materials Research, 2002, 17, 107-114.	2.6	38
71	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	38
72	Atomic Layer Deposition of SrS and BaS Thin Films Using Cyclopentadienyl Precursors. Chemistry of Materials, 2002, 14, 1937-1944.	6.7	37

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73	HfO[sub 2] Films Grown by ALD Using Cyclopentadienyl-Type Precursors and H[sub 2]O or O[sub 3] as Oxygen Source. Journal of the Electrochemical Society, 2006, 153, F39.	2.9	37
74	Hardening Mechanisms in Graphitic Carbon Nitride Films Grown with N2/Ar Ion Assistance. Chemistry of Materials, 2001, 13, 129-135.	6.7	35
75	Low-energy heavy-ion TOF-ERDA setup for quantitative depth profiling of thin films. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 5144-5150.	1.4	35
76	Atomic Layer Deposition of LiF Thin Films from Lithd, Mg(thd)₂, and TiF₄ Precursors. Chemistry of Materials, 2013, 25, 1656-1663.	6.7	35
77	Influence of thickness and growth temperature on the properties of zirconium oxide films grown by atomic layer deposition on silicon. Thin Solid Films, 2002, 410, 53-60.	1.8	34
78	Atomic layer deposition of calcium oxide and calcium hafnium oxide films using calcium cyclopentadienyl precursor. Thin Solid Films, 2006, 500, 322-329.	1.8	33
79	Atomic layer deposition of HfO2 thin films and nanolayered HfO2â€“Al2O3â€“Nb2O5 dielectrics. Journal of Materials Science: Materials in Electronics, 2003, 14, 361-367.	2.2	32
80	Influence of plasma chemistry on impurity incorporation in AlN prepared by plasma enhanced atomic layer deposition. Journal Physics D: Applied Physics, 2013, 46, 505502.	2.8	32
81	The production of the new cubic FeN phase by reactive magnetron sputtering. Applied Surface Science, 1999, 138-139, 261-265.	6.1	31
82	High quality superconducting titanium nitride thin film growth using infrared pulsed laser deposition. Superconductor Science and Technology, 2018, 31, 055017.	3.5	31
83	Evaluation of New Aminoalkoxide Precursors for Atomic Layer Deposition. Growth of Zirconium Dioxide Thin Films and Reaction Mechanism Studies. Chemistry of Materials, 2004, 16, 5630-5636.	6.7	30
84	Nucleation and growth of ZnO on PMMA by low-temperature atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	30
85	Atomic Layer Deposition of Strontium Tantalate Thin Films from Bimetallic Precursors and Water. Journal of the Electrochemical Society, 2004, 151, F69.	2.9	29
86	Atomic Layer Deposition of High-Permittivity Yttrium-Doped HfO[sub 2] Films. Electrochemical and Solid-State Letters, 2009, 12, G1.	2.2	29
87	Atomic Layer Deposition of Titanium Nitride Thin Films Using tert-Butylamine and Allylamine as Reductive Nitrogen Sources. Electrochemical and Solid-State Letters, 2002, 5, C4.	2.2	28
88	Broadband semiconductor saturable absorber mirrors in the 1.55-Î¼m wavelength range for pulse generation in fiber lasers. IEEE Journal of Quantum Electronics, 2002, 38, 369-374.	1.9	27
89	Atomic Layer Deposition of Hafnium Dioxide Films from Hafnium Hydroxylamide and Water. Chemical Vapor Deposition, 2004, 10, 91-96.	1.3	27
90	Atomic layer deposition of Ru films from bis(2,5-dimethylpyrrolyl)ruthenium and oxygen. Thin Solid Films, 2012, 520, 2756-2763.	1.8	27

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91	Programmable proximity aperture lithography with MeV ion beams. Journal of Vacuum Science & Technology B, 2008, 26, 1732.	1.3	25
92	Round Robin: measurement of H implantation distributions in Si by elastic recoil detection. Nuclear Instruments & Methods in Physics Research B, 2004, 222, 547-566.	1.4	23
93	Properties of Oxide Film Atomic Layer Deposited from Tetraethoxy Silane, Hafnium Halides, and Water. Journal of the Electrochemical Society, 2004, 151, F98.	2.9	23
94	Studies on atomic layer deposition of IRMOF-8 thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	23
95	Structural and chemical analysis of annealed plasma-enhanced atomic layer deposition aluminum nitride films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	22
96	Hafnium tetraiodide and oxygen as precursors for atomic layer deposition of hafnium oxide thin films. Thin Solid Films, 2002, 418, 69-72.	1.8	20
97	Broadband Ultrahigh-Resolution Spectroscopy of Particle-Induced X Rays: Extending the Limits of Nondestructive Analysis. Physical Review Applied, 2016, 6, .	3.8	20
98	Thermal atomic layer deposition of AlOxNy thin films for surface passivation of nano-textured flexible silicon. Solar Energy Materials and Solar Cells, 2019, 193, 231-236.	6.2	20
99	Antiferromagnetism and pâ€type conductivity of nonstoichiometric nickel oxide thin films. InformaÄnÃ MateriÃ¡ly, 2020, 2, 769-774.	17.3	20
100	Room-temperature plasma-enhanced atomic layer deposition of ZnO: Film growth dependence on the PEALD reactor configuration. Surface and Coatings Technology, 2017, 326, 281-290.	4.8	19
101	Atomic layer deposition of AlN from AlCl3 using NH3 and Ar/NH3 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	19
102	Effects of surface roughness on results in elastic recoil detection measurements. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 235-239.	1.4	18
103	Fabrication of microfluidic devices using MeV ion beam Programmable Proximity Aperture Lithography (PPAL). Nuclear Instruments & Methods in Physics Research B, 2008, 266, 2461-2465.	1.4	18
104	Transition-Edge Sensors for Particle Induced X-ray Emission Measurements. Journal of Low Temperature Physics, 2014, 176, 285-290.	1.4	18
105	Effect of ozone concentration on silicon surface passivation by atomic layer deposited Al2O3. Applied Surface Science, 2015, 357, 2402-2407.	6.1	18
106	Characterization and Electrochemical Properties of Oxygenated Amorphous Carbon (a-C) Films. Electrochimica Acta, 2016, 220, 137-145.	5.2	18
107	Investigation of ZrO[sub 2]â€"Gd[sub 2]O[sub 3] Based High-k Materials as Capacitor Dielectrics. Journal of the Electrochemical Society, 2010, 157, G202.	2.9	17
108	Atomic layer deposited lithium aluminum oxide: (In)dependency of film properties from pulsing sequence. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	17

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109	Mechanical and optical properties of as-grown and thermally annealed titanium dioxide from titanium tetrachloride and water by atomic layer deposition. Thin Solid Films, 2021, 732, 138758.	1.8	17
110	Effect of preparation conditions on properties of atomic layer deposited TiO2 films in Moâ€“TiO2â€“Al stacks. Thin Solid Films, 2006, 510, 39-47.	1.8	16
111	Development of an MeV ion beam lithography system in JyvÃ¤skylÃ¤. Nuclear Instruments & Methods in Physics Research B, 2007, 260, 77-80.	1.4	16
112	Lithography exposure characteristics of poly(methyl methacrylate) (PMMA) for carbon, helium and hydrogen ions. Nuclear Instruments & Methods in Physics Research B, 2012, 272, 162-164.	1.4	16
113	Ti Alloyed Î±-Ga2O3: Route towards Wide Band Gap Engineering. Micromachines, 2020, 11, 1128.	2.9	16
114	Experimental Linear Energy Transfer of Heavy Ions in Silicon for RADEF Cocktail Species. IEEE Transactions on Nuclear Science, 2009, 56, 2242-2246.	2.0	15
115	Atomic Layer Deposition and Characterization of Aluminum Silicate Thin Films for Optical Applications. Journal of the Electrochemical Society, 2011, 158, P15.	2.9	15
116	Low-temperature atomic layer deposition of SiO ₂ /Al ₂ O ₃ multilayer structures constructed on self-standing films of cellulose nanofibrils. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2018, 376, 20170037.	3.4	15
117	Al2O3 ALD films grown using TMAâ€ +â€ rare isotope 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si2.svg"><mml:mrow><mml:msubsup><mml:mrow><mml:mtext>H</mml:mtext></mml:mrow><mml:mrow><mml:mn>2</m and 1<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si3.svg"><mml:mrow><mml:msubsup><mml:mrow><mml:mtext>H</mml:mtext></mml:mrow><mml:mrow><mml:mn>2</m Applied Surface Science, 2021, 546, 148909.	6.1	15
118	Hafnium silicon oxide films prepared by atomic layer deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 2-5.	3.5	14
119	Growth of osteoblasts on lithographically modified surfaces. Nuclear Instruments & Methods in Physics Research B, 2007, 260, 130-135.	1.4	14
120	Depth profiling of Al2O3+TiO2 nanolaminates by means of a time-of-flight energy spectrometer. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 3021-3024.	1.4	14
121	Blistering mechanisms of atomic-layer-deposited AlN and Al2O3 films. Applied Physics Letters, 2017, 111, .	3.3	14
122	Low friction ta-C films with hydrogen reservoirs. Diamond and Related Materials, 2001, 10, 1030-1035.	3.9	13
123	Porous inorganicâ€“organic hybrid material by oxygen plasma treatment. Journal of Micromechanics and Microengineering, 2011, 21, 125003.	2.6	13
124	Energy-loss straggling of 2â€“10 MeV/u Kr ions in gases. European Physical Journal D, 2013, 67, 1.	1.3	13
125	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO2 on a silicon substrate. Wear, 2015, 342-343, 270-278.	3.1	13
126	Ozoneâ€Based Atomic Layer Deposition of Al₂O₃ from Dimethylaluminum Chloride and Its Impact on Silicon Surface Passivation. Advanced Electronic Materials, 2017, 3, 1600491.	5.1	13

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127	Dynamics of photoluminescence in GaInNAs saturable absorber mirrors. Applied Physics A: Materials Science and Processing, 2003, 77, 861-863.	2.3	12
128	ALD of Ta(Si)N Thin Films Using TDMAS as a Reducing Agent and as a Si Precursor. Journal of the Electrochemical Society, 2004, 151, G523.	2.9	12
129	Chemically guided epitaxy of Rb-irradiated Î±-quartz. Journal of Applied Physics, 2004, 95, 4705-4713.	2.5	12
130	Plasma etch characteristics of aluminum nitride mask layers grown by low-temperature plasma enhanced atomic layer deposition in SF6 based plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	12
131	Excellent silicon surface passivation using dimethylaluminium chloride as Al source for atomic layer deposited Al₂O₃. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1795-1799.	1.8	12
132	Lowâ€Temperature Atomic Layer Deposition of Highâ€<i>k</i> SbO<i>_x</i> for Thin Film Transistors. Advanced Electronic Materials, 2022, 8, .	5.1	12
133	Wettability and compositional analysis of hydroxyapatite films modified by low and high energy ion irradiation. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 2515-2519.	1.4	11
134	Atomic Layer Deposition and Characterization of Erbium Oxide-Doped Zirconium Oxide Thin Films. Journal of the Electrochemical Society, 2010, 157, G193.	2.9	11
135	Recent negative ion source activity at JYFL. AIP Conference Proceedings, 2013, , .	0.4	11
136	Low-Temperature Molecular Layer Deposition Using Monofunctional Aromatic Precursors and Ozone-Based Ring-Opening Reactions. Langmuir, 2017, 33, 9657-9665.	3.5	11
137	Epitaxial recrystallization of amorphized Î±-quartz after sodium ion implantation and oxygen annealing. Surface and Coatings Technology, 2002, 158-159, 436-438.	4.8	10
138	Blue- and green-emitting SrS:Cu electroluminescent devices deposited by the atomic layer deposition technique. Journal of Applied Physics, 2003, 94, 3862-3868.	2.5	10
139	The analysis of a thin SiO2/Si3N4/SiO2 stack: A comparative study of low-energy heavy ion elastic recoil detection, high-resolution Rutherford backscattering and secondary ion mass spectrometry. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 847-850.	1.4	10
140	Depth resolution optimization for low-energy ERDA. Nuclear Instruments & Methods in Physics Research B, 2007, 261, 512-515.	1.4	10
141	Oxy-nitrides characterization with a new ERD-TOF system. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 112-114.	1.4	10
142	Comparison of mechanical properties and composition of magnetron sputter and plasma enhanced atomic layer deposition aluminum nitride films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	10
143	Structural and Optical Characterization of ZnS Ultrathin Films Prepared by Low-Temperature ALD from Diethylzinc and 1.5-Pentanedithiol after Various Annealing Treatments. Materials, 2019, 12, 3212.	2.9	10
144	Nanoscale etching of III-V semiconductors in acidic hydrogen peroxide solution: GaAs and InP, a striking contrast in surface chemistry. Applied Surface Science, 2019, 465, 596-606.	6.1	10

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145	What Determines the Electrochemical Properties of Nitrogenated Amorphous Carbon Thin Films?. Chemistry of Materials, 2021, 33, 6813-6824.	6.7	10
146	Ion beam mixing in Fe/Si and Ta/Si bilayers: Possible effects of ion charges. Nuclear Instruments & Methods in Physics Research B, 2003, 205, 741-745.	1.4	9
147	Aperture-edge scattering in MeV ion-beam lithography. II. Scattering from a rectangular aperture. Journal of Vacuum Science & Technology B, 2009, 27, 1109.	1.3	9
148	Characterization of surface layers in Zn-diffused LiNbO3 waveguides by heavy ion elastic recoil detection. Applied Physics Letters, 2002, 81, 1981-1983.	3.3	8
149	The impact of the density and type of reactive sites on the characteristics of the atomic layer deposited WNxCy films. Journal of Applied Physics, 2006, 99, 063515.	2.5	8
150	Time-of-flight ERD with a 200mm2 Si3N4 window gas ionization chamber energy detector. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 271-274.	1.4	8
151	Normal-Metalâ€"Insulatorâ€"Superconductor Tunnel Junction With Atomic-Layer-Deposited Titanium Nitride as Superconductor. IEEE Transactions on Applied Superconductivity, 2015, 25, 1-4.	1.7	8
152	Aluminum tri-isopropoxide as an alternative precursor for atomic layer deposition of aluminum oxide thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	8
153	TOF-ERDA spectrometry applied for the analysis of Be migration in (100) GaAs. Nuclear Instruments & Methods in Physics Research B, 1998, 139, 225-229.	1.4	7
154	Effect of isotopic substitution on IR and ESR properties of mass selected ion beam deposited ta-C films. Diamond and Related Materials, 2003, 12, 900-904.	3.9	7
155	Hâ€"Li correlation and stoichiometry of mixed phases in proton-exchanged LiNbO[sub 3] waveguides. Journal of Applied Physics, 2003, 94, 7710.	2.5	7
156	Resolution Performance of Programmable Proximity Aperture MeV Ion Beam Lithography System. Materials Research Society Symposia Proceedings, 2007, 1020, 1.	0.1	7
157	New experimental molecular stopping cross section data of Al2O3, for heavy ions. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 341-345.	1.4	7
158	Secondary electron flight times and tracks in the carbon foil time pick-up detector. Nuclear Instruments & Methods in Physics Research B, 2014, 336, 55-62.	1.4	7
159	The<i>Î±</i>and<i>Î³</i>plasma modes in plasma-enhanced atomic layer deposition with O₂â€"N₂capacitive discharges. Journal Physics D: Applied Physics, 2017, 50, 095201.	2.8	7
160	Tribological properties of thin films made by atomic layer deposition sliding against silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	7
161	Roomâ€Temperature Micropillar Growth of Lithiumâ€"Titanateâ€"Carbon Composite Structures by Selfâ€Biased Direct Current Magnetron Sputtering for Lithium Ion Microbatteries. Advanced Functional Materials, 2019, 29, 1904306.	14.9	7
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